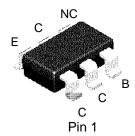


FMBS549



Package: SuperSOT-6 single

Mark: .S1

PNP Low Saturation Transistor

This device is designed with high current gain and low saturation voltage with collector currents up to 2A continous. Sourced from process PB.

Absolute Maximum Ratings* T_{A = 25°C unless otherwise noted}

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	30	V
V _{CBO}	Collector-Base Voltage	35	V
V _{EBO}	Emitter-Base Voltage	5	V
Ic	Collector Current- Continuous - Peak Pulse Current	1 2	A A
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics T_{A = 25°C unless otherwise noted}

Symbol	Characteristics	Max	Units
P _D	Total Device Dissipation*	700	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, total	180	°C/W

^{*}Device mounted on a 1 in2 pad of 2 oz copper.

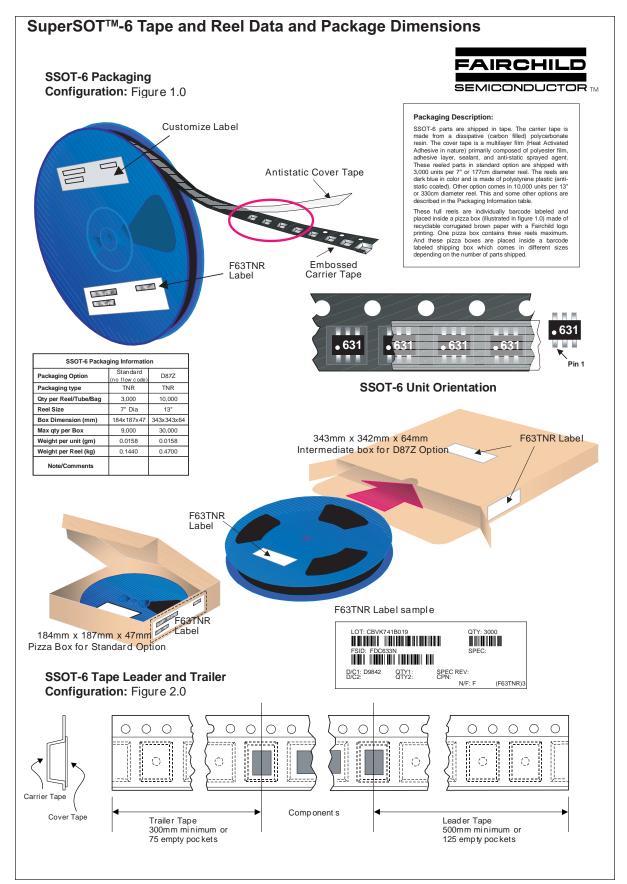
¹⁾ These ratings are based on a maximum junction temperature of 150°C.

²⁾ These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

PNP Low Saturation transistor (continued)

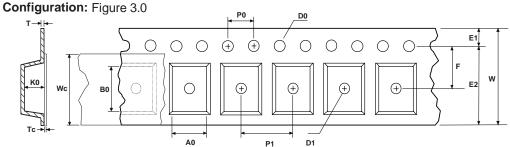
_	IAA+riaa	Characteristics TA = 25°C unles	
	ech icai		

Symbol	Parameter Test Conditions		Min	Max	Units	
OFF CHA	RACTERISTICS					
BV _{CEO}	Collector to Emitter Voltage	Ic = 10 mA	30		V	
BV _{CBO}	Collector to Base Voltage	Ic = 100 uA	35		V	
BV _{EBO}	Emitter to Base Voltage	le = 100 uA	5		V	
I _{CBO}	Collector Cutoff Current	Vcb = 30 V Vcb = 30 V, Ta= 100C		100 10	nA uA	
I _{EBO}	Emitter Cutoff Current	Veb = 4 V		100	nA	
ON CHAR	RACTERISTICS					
h _{FE}	DC Current Gain	Vce = 2V, Ic = 50 mA Vce = 2V, Ic = 500 mA Vce = 2V, Ic = 1 A Vce = 2V, Ic = 2 A Vce = 0.8V, Ic = 500 m A	70 100 80 40 100	300	-	
VCE(sat)	Collector-Emitter Saturation Voltage	Ic = 250 mA, Ib = 25 mA Ic = 500 mA, Ib = 50 mA Ic = 1 A, Ib = 100 mA Ic = 2 A, Ib = 200 mA		200 350 500 750	mV mV mV	
V _{BE(sat)}	Base-Emitter Saturation Voltage	Ic = 1 A, Ib = 100 mA		1.25	V	
V _{BE(on)}	Base-Emitter On Voltage	Ic = 1 A, Vce = 2 V		1	V	
SMALL S	IGNAL CHARACTERISTICS					
C _{obo}	Output Capacitance	Vcb = 10V, f = 1MHz		25	pF	
f _T	Current Gain - Bandwidth Product	Vce = 5 V, Ic = 100mA, f = 100MHz	100		MHz	





SSOT-6 Embossed Carrier Tape



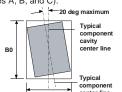


Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SSOT-6 (8mm)	3.23 +/-0.10	3.18 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.37 +/-0.10	0.255 +/-0.150	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

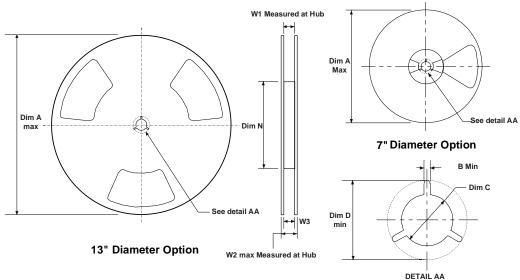


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

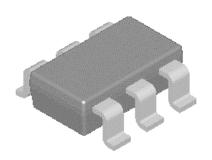
SSOT-6 Reel Configuration: Figure 4.0

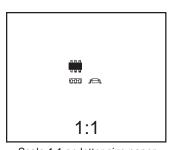


Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

SuperSOT™-6 Tape and Reel Data and Package Dimensions, continued

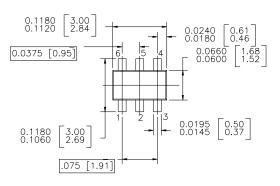
SuperSOT -6 (FS PKG Code 31, 33)

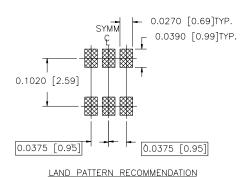




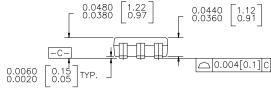
Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

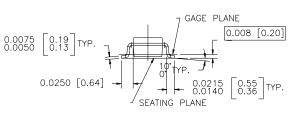
Part Weight per unit (gram): 0.0158





CONTROLLING DIMENSION IS INCH VALUES IN [] ARE MILLIMETERS





NOTES: UNLESS OTHERWISE SPECIFIED

1.0 STANDARD LEAD FINISH: 150 MICROINCHES 93.81 MICROMETERS) MINIMUM TIN / LEAD (SOLDER) ON COPPER.

 $2.0\ \mathsf{NO}\ \mathsf{JEDEC}\ \mathsf{REGISTRATION}\ \mathsf{AS}\ \mathsf{OF}\ \mathsf{JULY}\ 1996$

SUPER SOT 6 LEADS

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